

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)	ATTY. DOCKET NO. 57810-093	SERIAL NO. 16/806,276
APPLICANT Hideaki FUJIWARA, et al.		
FILING DATE March 23, 2004	GROUP 2813	

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number + Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
D B		JP P2002-94058A	03/29/2002	TOSHIBA CORP		(Japan w/English Abstract)	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>DB</i>		Brian DOYLE, et al. "Transistor Elements for 30nm Physical Gate Lengths and Beyond", Intel Technology Journal, Vol. 6, Issue 2, May 16, 2002, ISSN 1535768X

EXAMINER

DATE CONSIDERED

1-6-05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.